

# RJK0206DPA

25V, 70A, 1.8mΩ max.

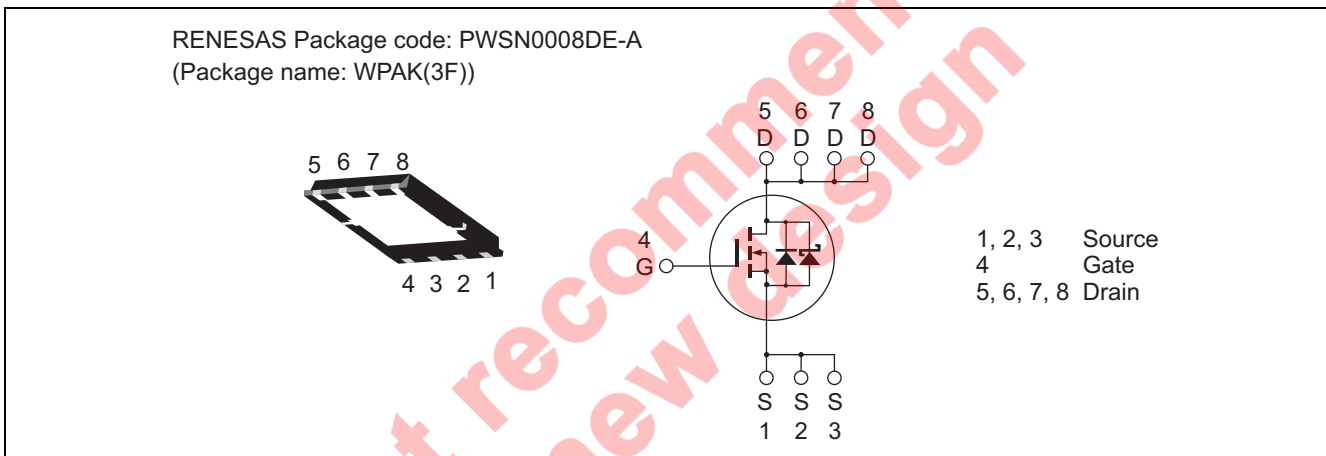
Built in SBD N Channel Power MOS FET  
High Speed Power Switching

R07DS0941EJ0400  
Rev.4.00  
Mar 21, 2013

## Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- Pb-free
- Halogen-free

## Outline



## Absolute Maximum Ratings

(Ta = 25°C)

| Item                                   | Symbol                                 | Ratings     | Unit |
|--|--|-------------|------|
| Drain to source voltage                | V <sub>DSS</sub>                       | 25          | V    |
| Gate to source voltage                 | V <sub>GSS</sub>                       | ±20         | V    |
| Drain current                          | I <sub>D</sub>                         | 70          | A    |
| Drain peak current                     | I <sub>D(pulse)</sub> <sup>Note1</sup> | 280         | A    |
| Body-drain diode reverse drain current | I <sub>DR</sub>                        | 70          | A    |
| Avalanche current                      | I <sub>AP</sub> <sup>Note 2</sup>      | 31          | A    |
| Avalanche energy                       | E <sub>AR</sub> <sup>Note 2</sup>      | 120         | mJ   |
| Channel dissipation                    | P <sub>ch</sub> <sup>Note3</sup>       | 65          | W    |
| Channel to case thermal impedance      | θ <sub>ch-c</sub> <sup>Note3</sup>     | 1.93        | °C/W |
| Channel temperature                    | T <sub>ch</sub>                        | 150         | °C   |
| Storage temperature                    | T <sub>stg</sub>                       | -55 to +150 | °C   |

- Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%  
2. Value at T<sub>ch</sub> = 25°C, R<sub>g</sub> ≥ 50 Ω  
3. T<sub>c</sub> = 25°C

## Electrical Characteristics

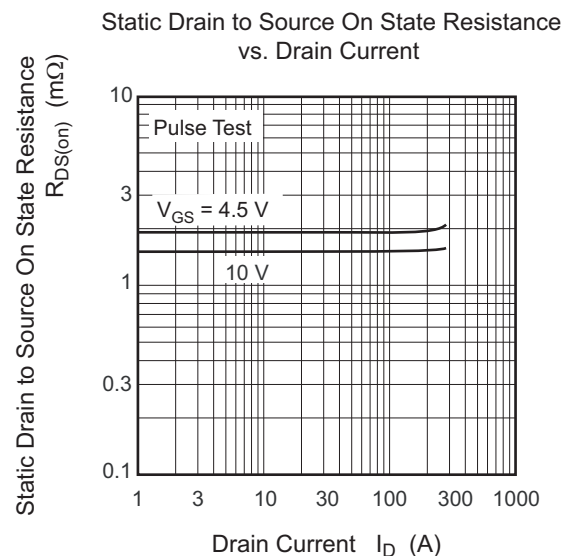
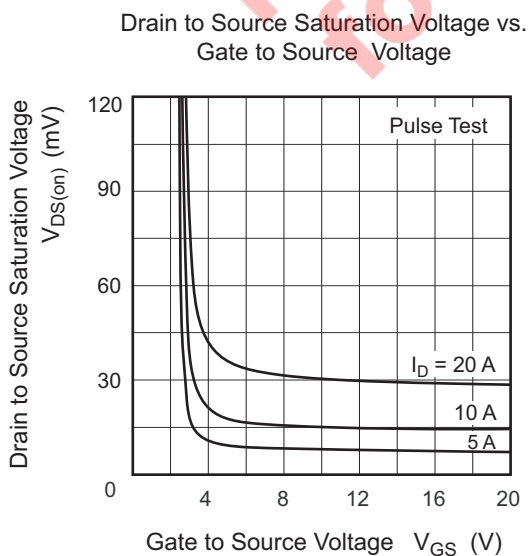
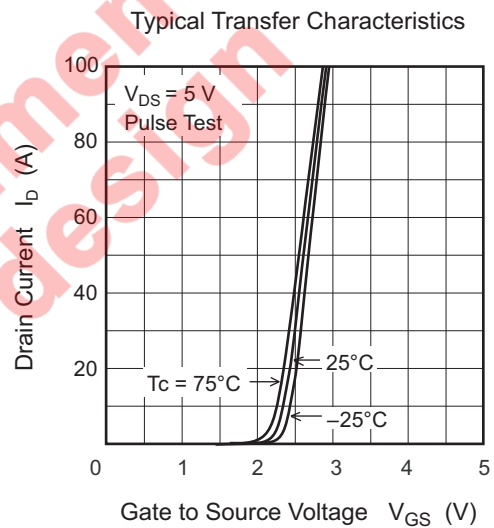
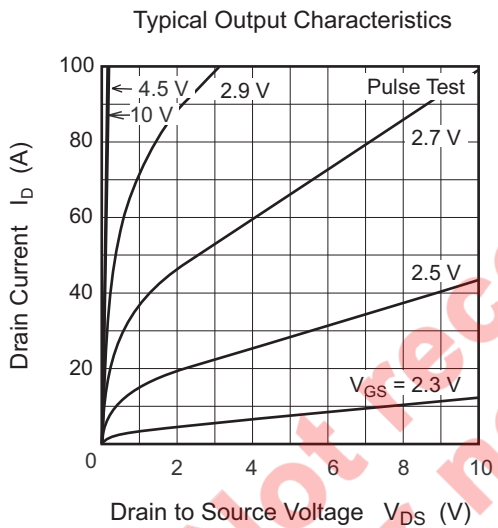
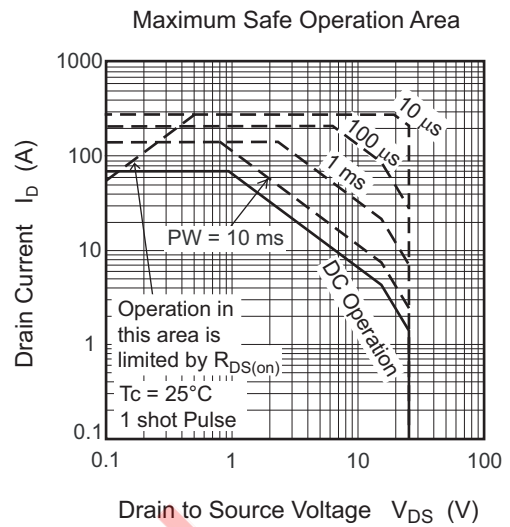
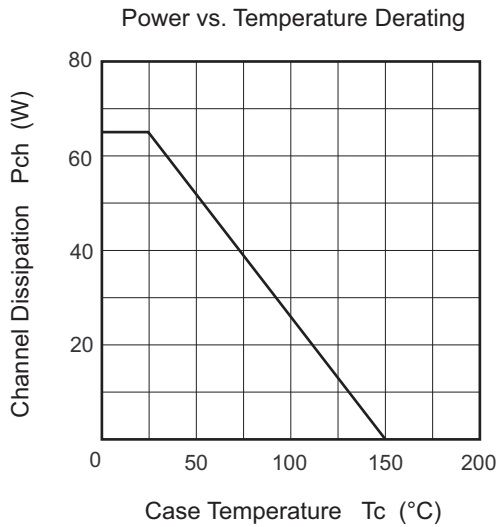
(Ta = 25°C)

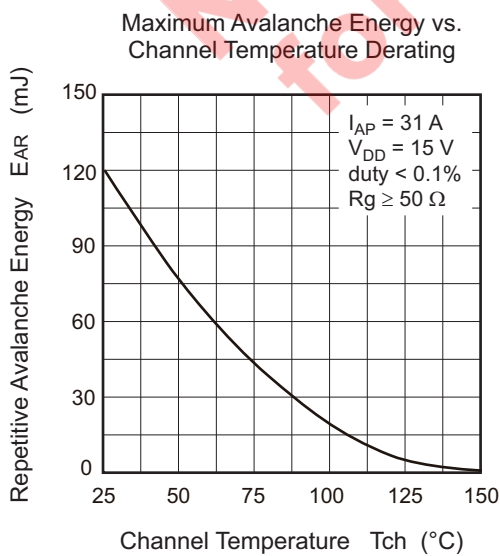
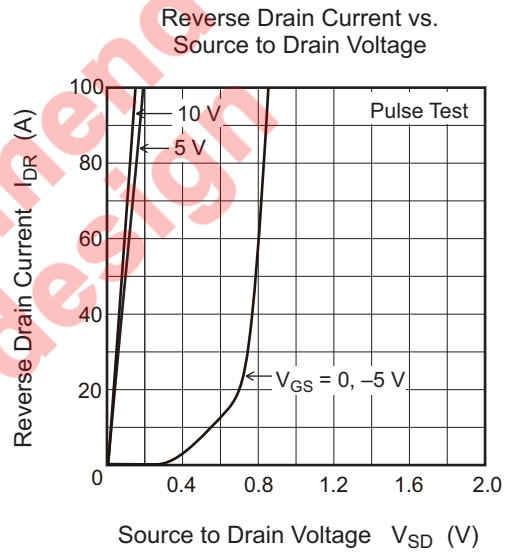
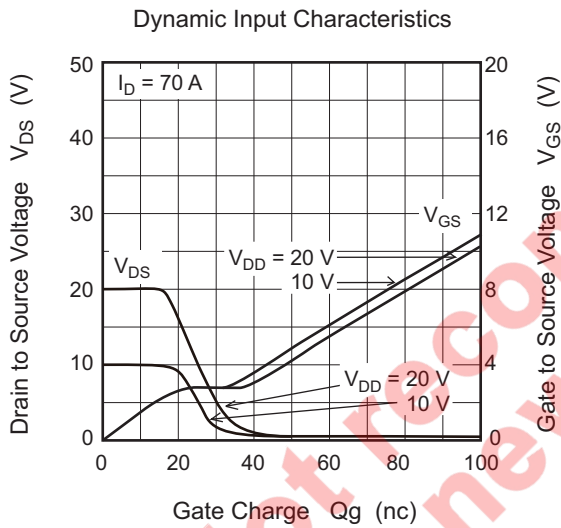
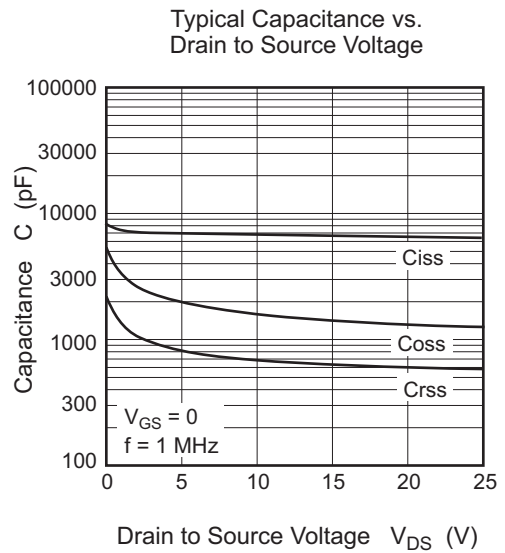
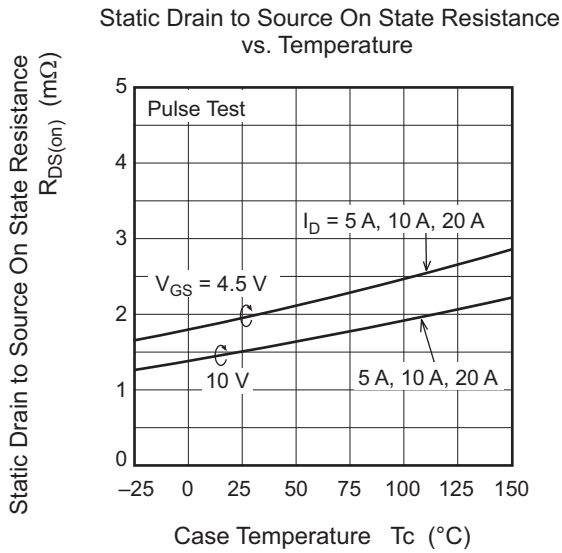
| Item                                       | Symbol        | Min | Typ  | Max       | Unit             | Test Conditions  |
|--|---------------|-----|------|-----------|------------------|--|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$ | 25  | —    | —         | V                | $I_D = 10 \text{ mA}$ , $V_{GS} = 0$   |
| Gate to source leak current                | $I_{GSS}$     | —   | —    | $\pm 0.5$ | $\mu\text{A}$    | $V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0$                                   |
| Zero gate voltage drain current            | $I_{DSS}$     | —   | —    | 1         | mA               | $V_{DS} = 25 \text{ V}$ , $V_{GS} = 0$                                       |
| Gate to source cutoff voltage              | $V_{GS(off)}$ | 1.2 | —    | 2.5       | V                | $V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$                               |
| Static drain to source on state resistance | $R_{DS(on)}$  | —   | 1.5  | 1.8       | $\text{m}\Omega$ | $I_D = 35\text{A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>                |
|  | $R_{DS(on)}$  | —   | 1.9  | 2.5       | $\text{m}\Omega$ | $I_D = 35\text{A}$ , $V_{GS} = 4.5 \text{ V}$ <sup>Note4</sup>               |
| Forward transfer admittance                | $ y_{fs} $    | —   | 140  | —         | S                | $I_D = 35 \text{ A}$ , $V_{DS} = 5 \text{ V}$ <sup>Note4</sup>               |
| Input capacitance                          | $C_{iss}$     | —   | 6790 | 9500      | pF               | $V_{DS} = 10 \text{ V}$  |
| Output capacitance                         | $C_{oss}$     | —   | 1600 | —         | pF               | $V_{GS} = 0$   |
| Reverse transfer capacitance               | $C_{rss}$     | —   | 680  | —         | pF               | $f = 1 \text{ MHz}$  |
| Gate Resistance                            | $R_g$         | —   | 1.5  | 3.0       | $\Omega$         |  |
| Total gate charge                          | $Q_g$         | —   | 44.5 | —         | nC               | $V_{DD} = 10 \text{ V}$  |
| Gate to source charge                      | $Q_{gs}$      | —   | 22.9 | —         | nC               | $V_{GS} = 4.5 \text{ V}$   |
| Gate to drain charge                       | $Q_{gd}$      | —   | 12.7 | —         | nC               | $I_D = 70 \text{ A}$   |
| Turn-on delay time                         | $t_{d(on)}$   | —   | 23   | —         | ns               | $V_{GS} = 10 \text{ V}$ , $I_D = 35 \text{ A}$                               |
| Rise time                                  | $t_r$         | —   | 8.7  | —         | ns               | $V_{DD} \cong 10 \text{ V}$  |
| Turn-off delay time                        | $t_{d(off)}$  | —   | 89   | —         | ns               | $R_L = 0.29\Omega$   |
| Fall time                                  | $t_f$         | —   | 30   | —         | ns               | $R_g = 4.7 \Omega$   |
| Body-drain diode forward voltage           | $V_{DF}$      | —   | 0.39 | —         | V                | $I_F = 2 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>                          |
| Body-drain diode reverse recovery time     | $t_{rr}$      | —   | 50   | —         | ns               | $I_F = 70 \text{ A}$ , $V_{GS} = 0$<br>$di_F/dt = 100 \text{ A}/\mu\text{s}$ |

Notes: 4. Pulse test

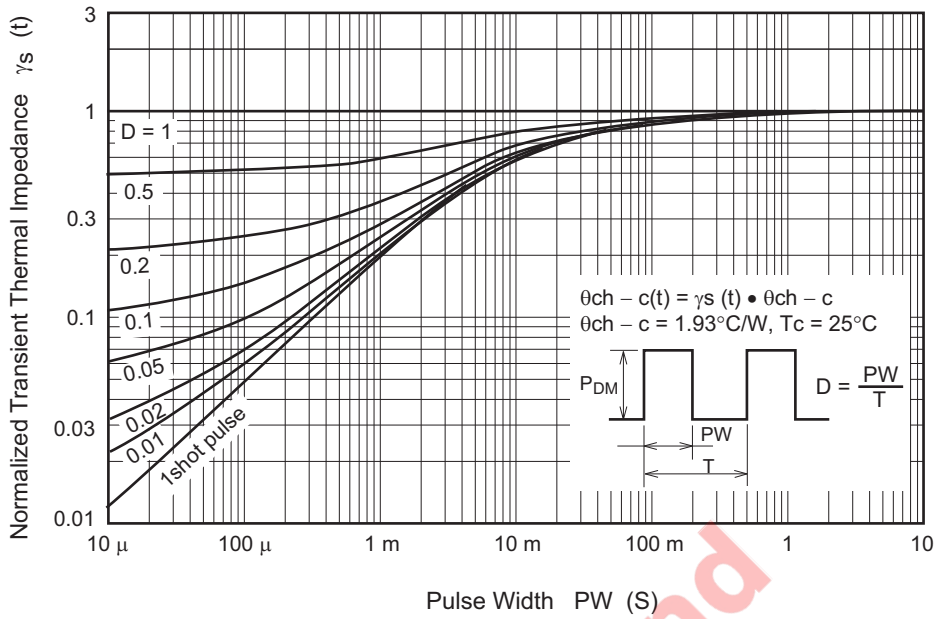
Not recommended for new designs

### Main Characteristics

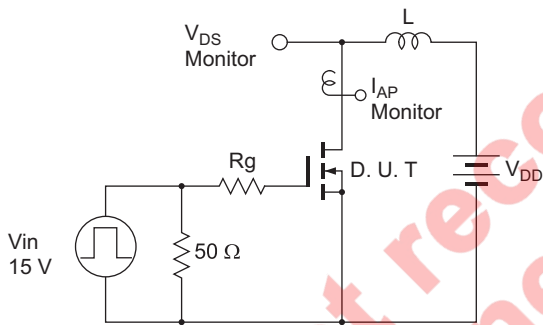




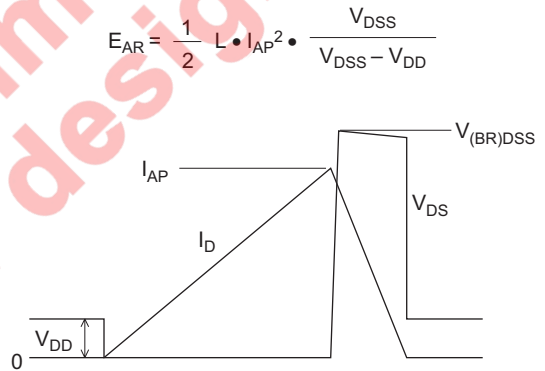
Normalized Transient Thermal Impedance vs. Pulse Width



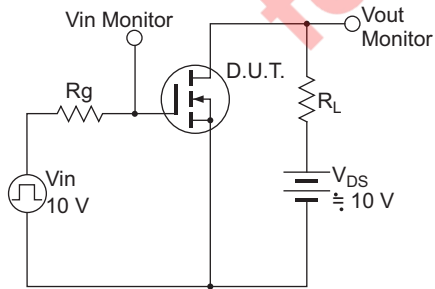
Avalanche Test Circuit



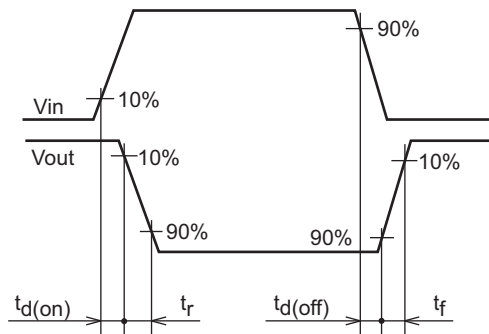
Avalanche Waveform



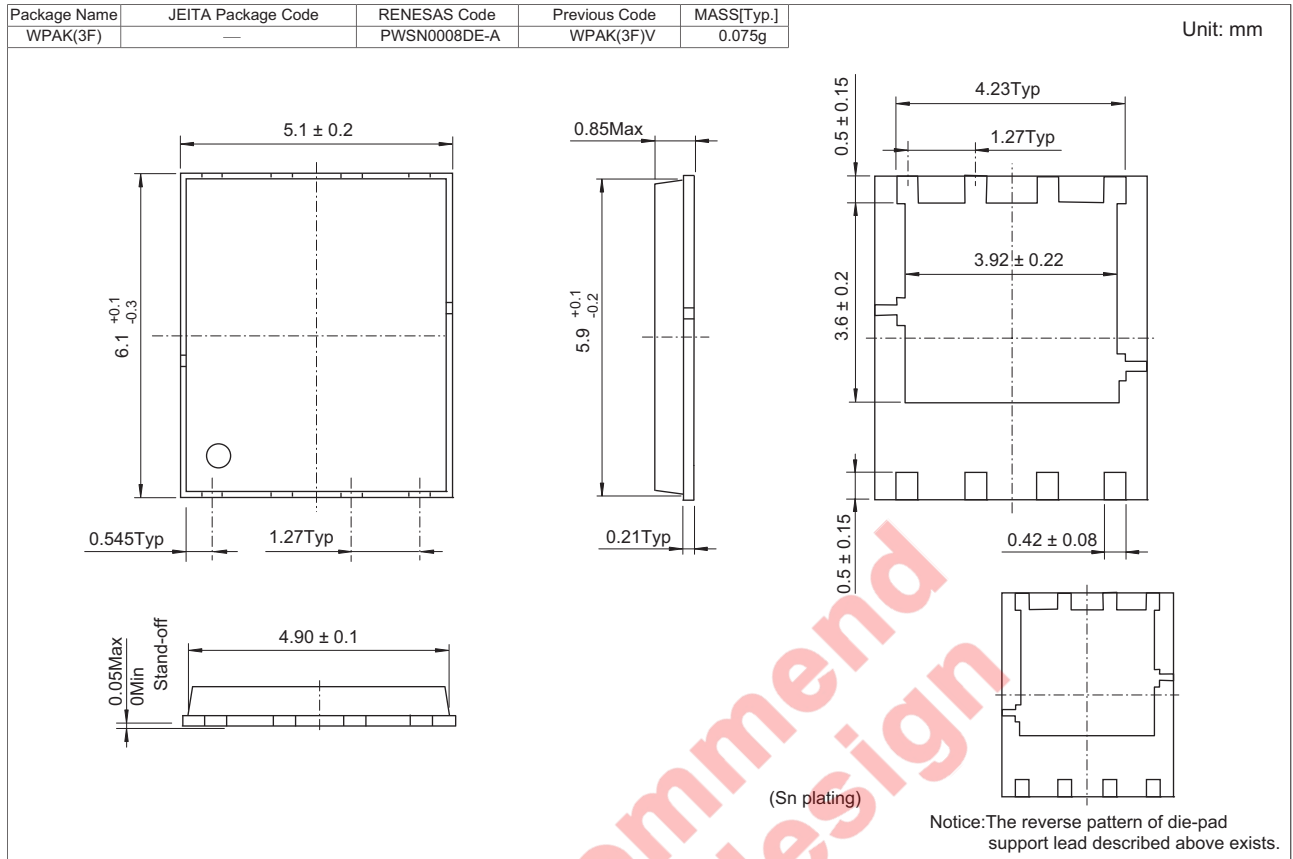
Switching Time Test Circuit



Switching Time Waveform



### Package Dimensions



### Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK0206DPA-00-J5A     | 3000 pcs | Taping             |

Note: The symbol of 2nd "-" is occasionally presented as "#".

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